

Application No.: 10/616,962

Docket No.: 21806-00113-US1

**AMENDMENTS TO THE SPECIFICATION**

The claims as filed in the original Specification are part of the disclosure. The following new paragraph does not constitute new matter, since the new paragraph represents claims 4 and 5, as originally presented, with changes only to the extent to ensure proper grammar and usage.

As stated in the MPEP, the Specification may be amended to include the claimed subject matter.<sup>1</sup> Accordingly, the subject matter of claims 4 and 5 has been added to the Specification as permitted by the MPEP.

Please add the following new paragraph to the Specification at page 6 between lines 5 and 6 as follows:

--In one aspect, the method of forming a crystalline polysilicon gate electrode structure on a gate dielectric may include controlling a variation of at least one of temperature, pressure, and flow rate of a continuous flow of silane or related silicon precursor species while depositing polysilicon in the silane or silicon precursor as crystals of correspondingly controlled grain size. Further, the variation may be controlled in step-wise manner, to thereby form a multi-region polycrystalline silicon deposit comprising regions having crystals of respective grain sizes.--

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<sup>1</sup> See MPEP §2163.06(III).